

January 2009

4N25M, 4N26M, 4N27M, 4N28M, 4N35M, 4N36M, 4N37M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M General Purpose 6-Pin Phototransistor Optocouplers

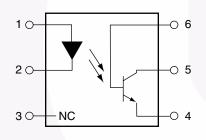
Features

- UL recognized (File # E90700, Volume 2)
- VDE recognized (File # 102497)
 - Add option V (e.g., 4N25VM)

Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

Schematic

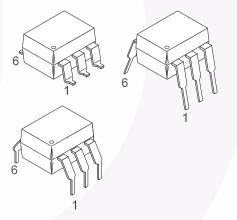


PIN 1. ANODE 2. CATHODE 3. NO CONNECTION 4. EMITTER 5. COLLECTOR 6. BASE

Description

The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.





Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units	
TOTAL DEV	CE	1		
T _{STG}	Storage Temperature	-40 to +150	°C	
T _{OPR}	Operating Temperature	-40 to +100	°C	
T _{SOL}	Wave solder temperature (see page 8 for reflow solder profile)	260 for 10 sec	°C	
PD	Total Device Power Dissipation @ T _A = 25°C	250	mW	
	Derate above 25°C	2.94		
EMITTER				
١ _F	DC/Average Forward Input Current	60	mA	
V _R	Reverse Input Voltage	6	V	
l _F (pk)	Forward Current – Peak (300µs, 2% Duty Cycle)	3	A	
PD	LED Power Dissipation @ T _A = 25°C	120	mW	
	Derate above 25°C	1.41	mW/°C	
DETECTOR				
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	70	V	
V _{ECO}	Emitter-Collector Voltage	7	V	
PD	Detector Power Dissipation @ T _A = 25°C	150	mW	
	Derate above 25°C	1.76	mW/°C	

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Individual Component Characteristics

	-					
Symbol	Parameter	Parameter Test Conditions		Тур.*	Max.	Unit
EMITTER		-			1	
V _F	Input Forward Voltage	I _F = 10mA		1.18	1.50	V
I _R	Reverse Leakage Current	V _R = 6.0V		0.001	10	μA
DETECTOR		i.		•		•
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1.0mA, I _F = 0	30	100		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm F} = 0$	70	120		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100μA, I _F = 0	7	10		V
I _{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10V, I_F = 0$		1	50	nA
I _{CBO}	Collector-Base Dark Current	V _{CB} = 10V			20	nA
C _{CE}	Capacitance	$V_{CE} = 0V$, f = 1 MHz		8		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec	7500			Vac(pk)
R _{ISO}	Isolation Resistance	V _{I-O} = 500 VDC	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance	V _{I-O} = &, f = 1MHz		0.2	2	pF

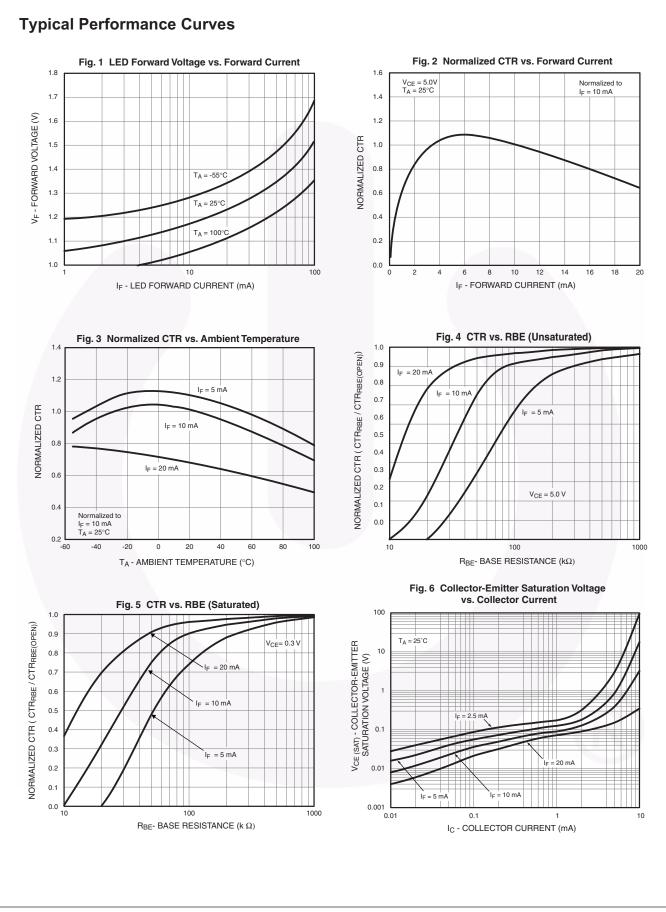
*Typical values at $T_A = 25^{\circ}C$

Electrical Characteristics (Continued) ($T_A = 25^{\circ}C$ unless otherwise specified)

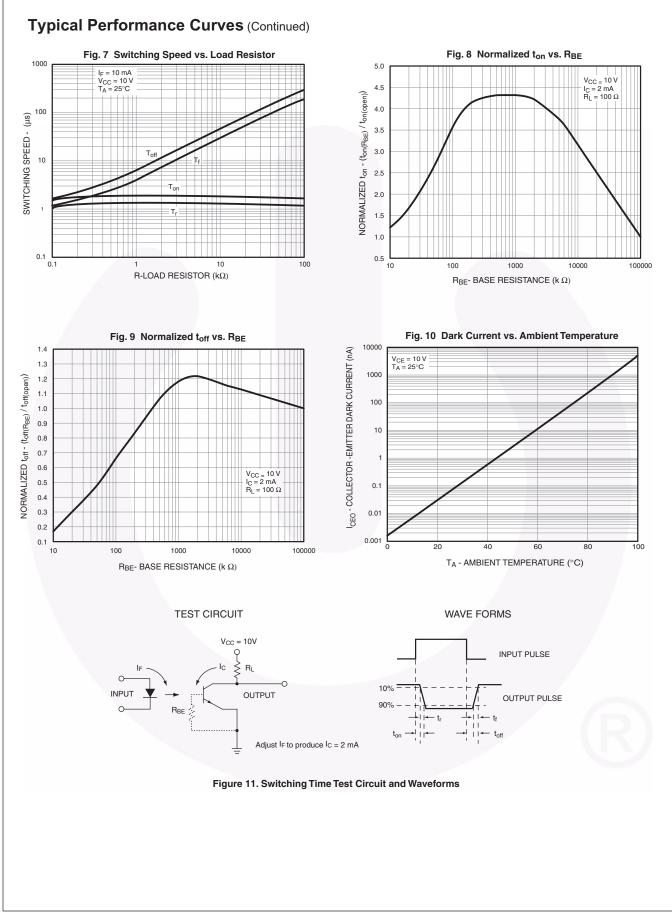
Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Тур.*	Max.	Unit
C CHARA	CTERISTICS				1		
CTR	Current Transfer Ratio, Collector to Emitter	$I_{\rm F} = 10 {\rm mA}, V_{\rm CE} = 10 {\rm V}$	4N35M, 4N36M, 4N37M	100			%
			H11A1M	50			
			H11A5M	30			
			4N25M, 4N26M H11A2M, H11A3M	20			1
			4N27M, 4N28M H11A4M	10			
		$I_F = 10mA, V_{CE} = 10V,$ $T_A = -55^{\circ}C$	4N35M, 4N36M, 4N37M	40			
		$I_F = 10mA, V_{CE} = 10V,$ $T_A = +100^{\circ}C$	4N35M, 4N36M, 4N37M	40			
	Collector-Emitter Saturation Voltage	$I_{\rm C} = 2$ mA, $I_{\rm F} = 50$ mA	4N25M, 4N26M, 4N27M, 4N28M,			0.5	V
		I _C = 0.5mA, I _F = 10mA	4N35M, 4N36M, 4N37M			0.3	
			H11A1M, H11A2M, H11A3M, H11A4M, H11A5M			0.4	
AC CHARA	CTERISTICS				1		
T _{ON} Non-Saturated Turn-on Time		$I_F = 10mA, V_{CC} = 10V,$ $R_L = 100\Omega$ (Fig. 11)	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4, H11A5M		2		μs
		$I_{C} = 2mA, V_{CC} = 10V,$ $R_{L} = 100\Omega \text{ (Fig. 11)}$	4N35M, 4N36M, 4N37M		2	10	μs
T _{OFF}	Turn-off Time	$I_{F} = 10mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M		2		μs
		$I_{C} = 2mA, V_{CC} = 10V,$ $R_{L} = 100\Omega$ (Fig. 11)	4N35M, 4N36M, 4N37M		2	10	

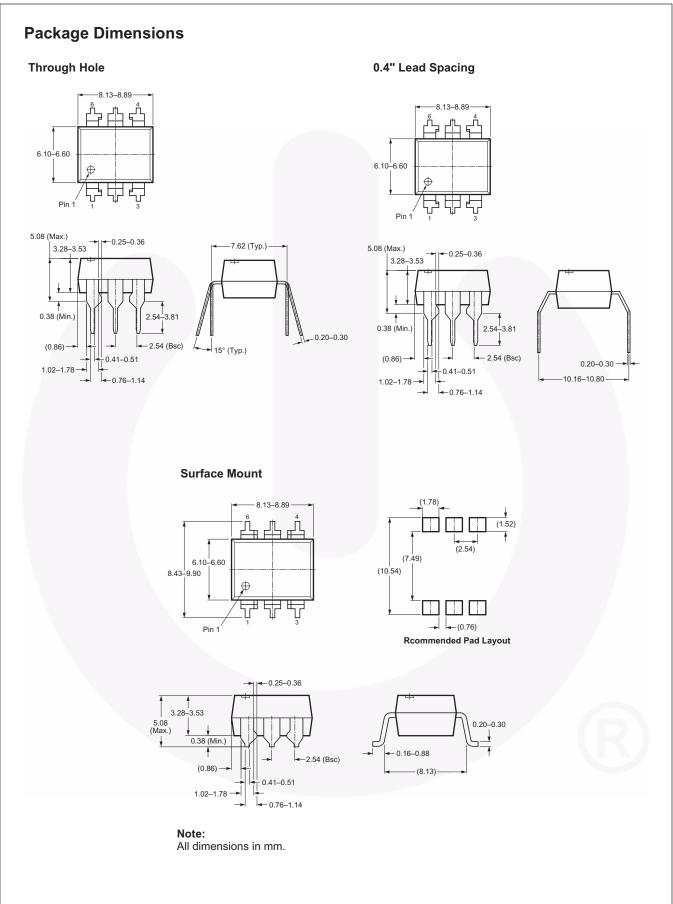
* Typical values at T_A = 25°C



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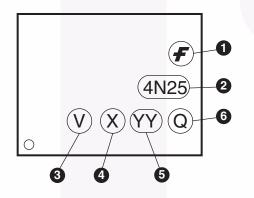
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Ordering Information

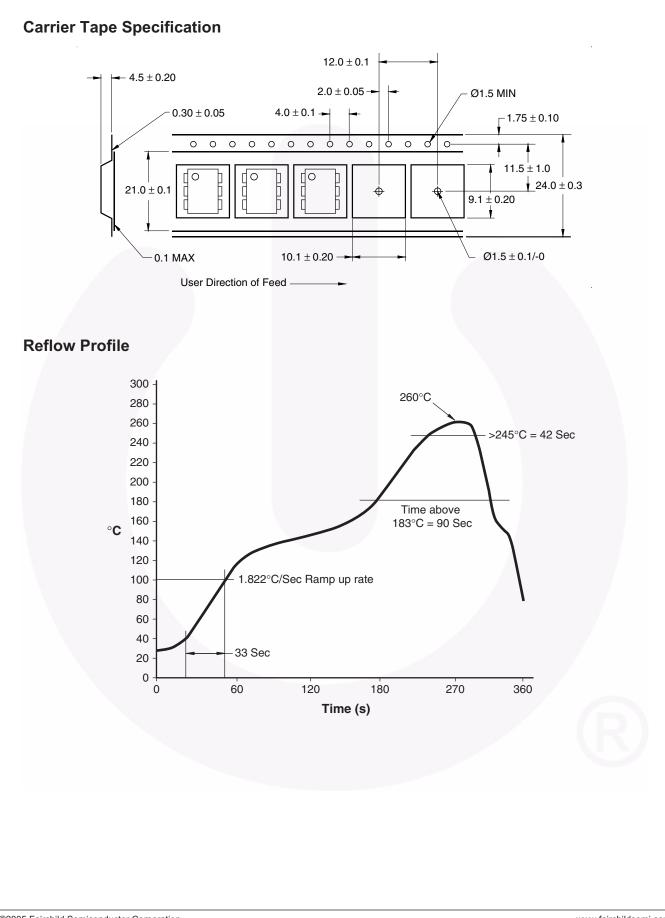
Option	Order Entry Identifier (Example)	Description
No option	4N25M	Standard Through Hole Device
S	4N25SM	Surface Mount Lead Bend
SR2	4N25SR2M	Surface Mount; Tape and Reel
Т	4N25TM	0.4" Lead Spacing
V	4N25VM	VDE 0884
TV	4N25TVM	VDE 0884, 0.4" Lead Spacing
SV	4N25SVM	VDE 0884, Surface Mount
SR2V	4N25SR2VM	VDE 0884, Surface Mount, Tape and Reel

Marking Information



Definitions1Fairchild logo2Device number3VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)4One digit year code, e.g., '7'5Two digit work week ranging from '01' to '53'6Assembly package code

*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.





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